

International Rectifier IRFK3D150, IRFK3F150

Isolated Base Power HEX-pak™ Assembly - Half Bridge Configuration

- High Current Capability.
- UL recognised E78996.
- Electrically Isolated Base Plate.
- Easy Assembly into Equipment.

Description

The HEX-pak™ utilises the well-proven HEXFET™ die, combining low on-state resistance with high transconductance. These superior technology die are assembled by state of the art techniques into the TO-240 package, featuring 2.5kV rms isolation and solid M5 screw connections. The small footprint means the package is highly suited to power applications where space is a premium. Available in two versions, IRFK.D... for fast switching and IRFK.F... for oscillation sensitive applications.

$$V_{DS} = 100V$$

$$R_{DS(on)} = 20m\Omega$$

$$I_D = 125A$$

Absolute Maximum Rating

Parameter	Max.	Units
$I_D @ T_C=25^\circ C$	125	A
$I_D @ T_C=100^\circ C$	55	A
I_{DM}	435	A ①
$P_D @ T_C=25^\circ C$	625	W
V_{GS}	20	V
V_{INS}	2.5	kV
T_J	-40 to 150	°C
T_{STG}	-40 to 150	°C

Thermal and Mechanical Specifications

Parameter	Min.	Typ.	Max.	Units
R_{thJC}	-	-	0.20	K/W ②
R_{thCS}	-	0.1	-	K/W
T	Mounting Torque +10%			③
	HEXpak to Heatsink	-	5	Nm
	Busbar to HEXpak	-	3	Nm ④
wt	Approximate Weight			g
	-	5	-	oz

Notes:

- ① - Repetitive Rating; Pulse width limited by maximum junction temperature see figure 8.
- ② - Per Module.
- ③ - A mounting compound is recommended and the torque should be rechecked after a period of three hours to allow for the spread of the compound.

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions	
B_{VDSS}	Drain-to-Source Breakdown voltage	100	-	-	V	$V_{GS}=0V, I_D=1.0mA$	
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	-	16	20	m Ω	$V_{GS}=10V, I_D=45A$	
$I_{D(on)}$	On-State Drain Current	125	-	-	A	$V_{DS} > I_{D(on)} \times R_{DS(on)}$, max., $V_{GS}=10V$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	-	4.0	V	$V_{DS}=V_{GS}, I_D=1.0mA$	
g_{fs}	Forward Transconductance ④	39	60	-	S	$V_{DS} > 50V, I_D=55A$	
I_{DSS}	Zero Gate Voltage Drain Current	-	-	0.75	mA	$V_{DS}=V_{DS,max}, V_{GS}=0V$	
		-	-	3.0	mA	$V_{GS}=10V, T_C=125^\circ\text{C}, V_{DS}=V_{DS,max} \times 0.8$	
I_{GSS}	Gate-to-Source Leakage Forward	-	-	300	nA	$V_{GS}=20V$	
I_{GSS}	Gate-to-Source Leakage Reverse	-	-	-300	nA	$V_{GS}=-20V$	
Q_g	Total Gate Charge	-	250	390	nC	$I_D=125A, V_{GS}=10V,$	
Q_{gs}	Gate-to-Source Charge	-	50	80	nC	$V_{DS}=V_{DS,max} \times 0.8$	
Q_{gd}	Gate-to-Drain ("Miller") Charge	-	132	195	nC		
$t_{d(on)}$	Turn-on Delay Time	-	65	-	ns	$V_{DD}=40V, I_D=55A,$	
t_r	Rise Time	IRFK3D150	-	75	-	ns	$V_{GS}=10V,$
		IRFK3F150	-	200	-	ns	
$t_{d(off)}$	Turn-off Delay Time	IRFK3D150	-	190	-	ns	$R_{SOURCE}=3.3\Omega$
		IRFK3F150	-	250	-	ns	
t_f	Fall Time	IRFK3D150	-	60	-	ns	
		IRFK3F150	-	100	-	ns	
L_{DS}	Drain-to-Source Inductance	-	18	-	nH		
C_{iss}	Input Capacitance	-	8.0	-	nF	$V_{GS}=0V, V_{DS}=25V,$	
C_{oss}	Output Capacitance	-	3.0	-	nF	$f=1.0MHz$	
C_{riss}	Reverse Transfer Capacitance	-	0.8	-	nF		
	Linear Derating Factor	-	-	5	W/K		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	-	-	125	A	
I_{SM}	Pulsed Source Current (Body Diode)	-	-	435	A	
V_{SD}	Diode Forward Voltage	-	-	2.5	V	$V_{GS}=0V, I_S=125A, T_C=25^\circ\text{C}$
t_{rr}	Reverse Recovery Time	100	210	420	ns	$di/dt=400A/\mu s, T_J=150^\circ\text{C}$
Q_{rr}	Reverse Recovered Charge	3.6	6.9	14.0	μC	$I_S=125A$

Notes:

④ - Pulse Width $\leq 300\mu s$; Duty cycle $\leq 2\%$.



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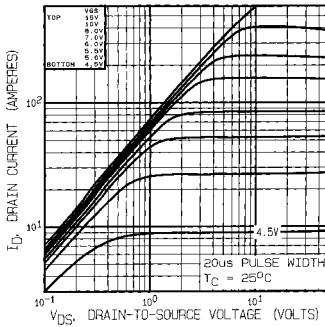


Fig 1. Typical Output Characteristics,
 $T_C = 25^\circ\text{C}$

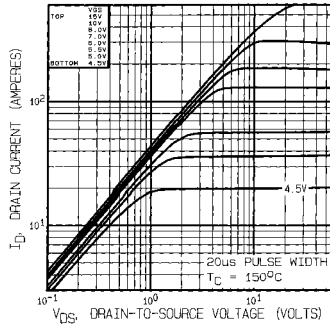


Fig 2. Typical Output Characteristics,
 $T_C = 150^\circ\text{C}$

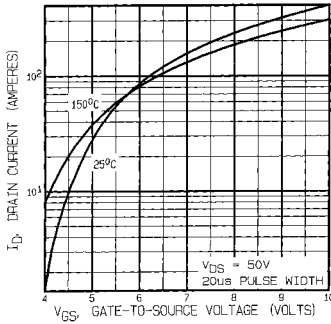


Fig 3. Typical Transfer Characteristics

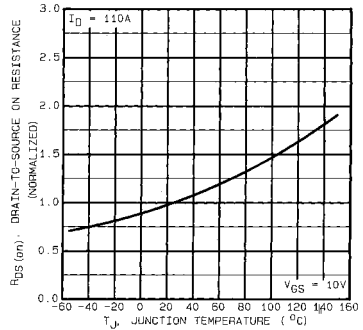


Fig 4. Normalized On-Resistance Vs.
Temperature

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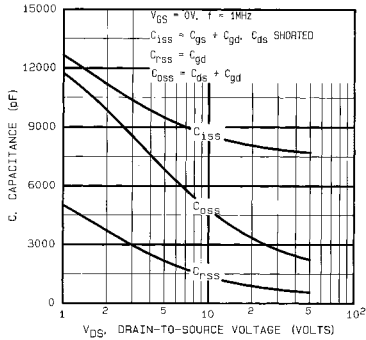


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

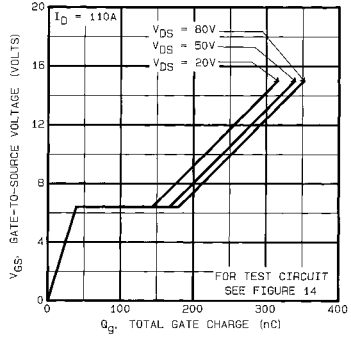


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

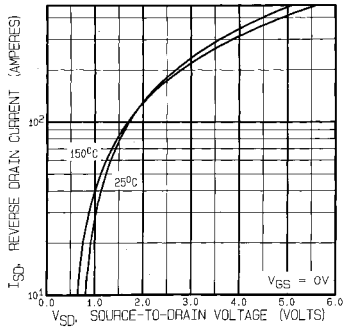


Fig 7. Typical Source-Drain Diode Forward Voltage

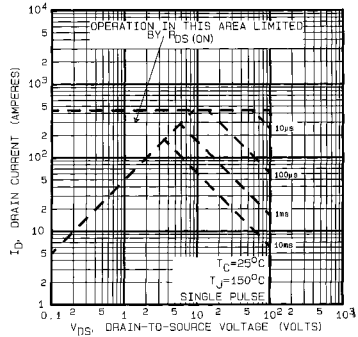


Fig 8. Maximum Safe Operating Area



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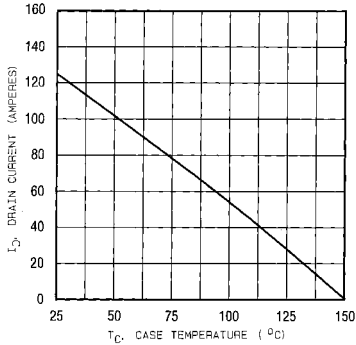


Fig 9. Maximum Drain Current Vs. Case Temperature

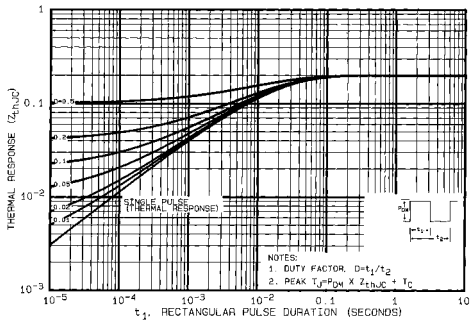


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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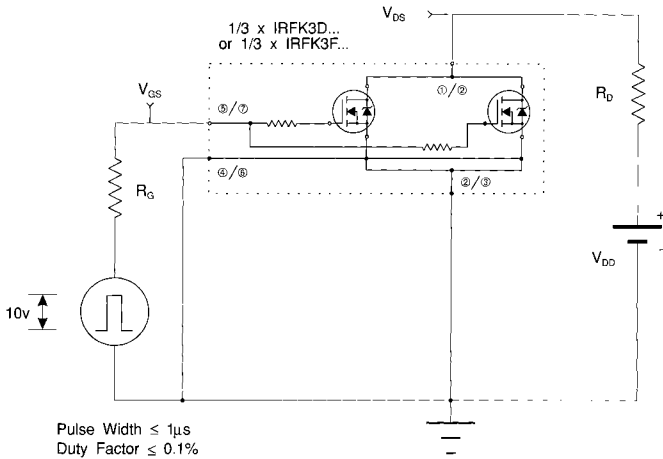


Fig 11a. Switching Time Test Circuit

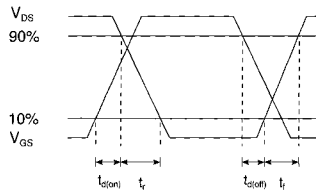
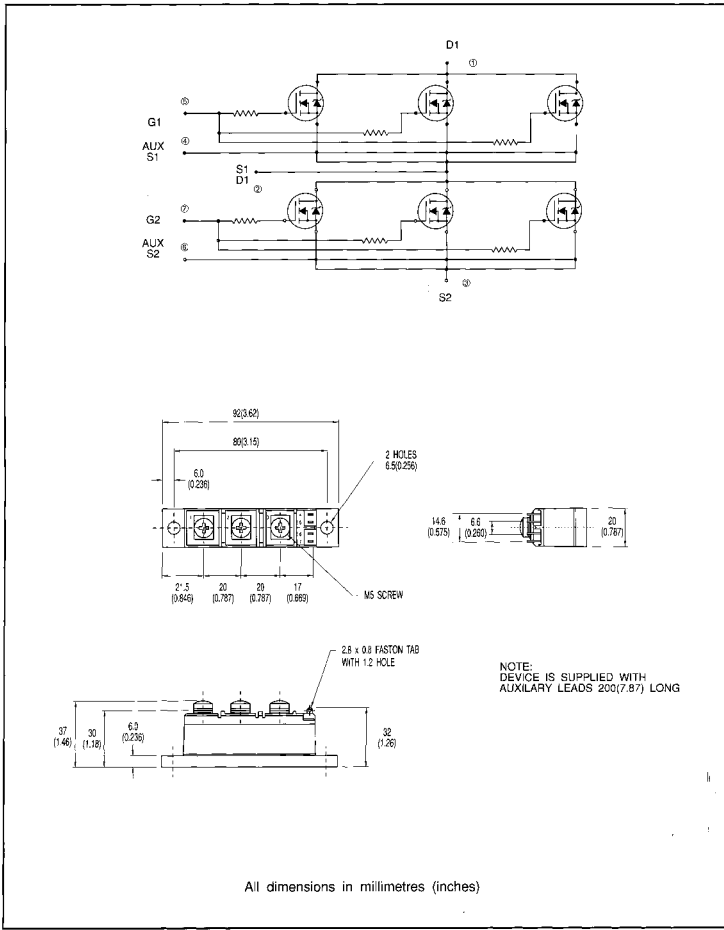


Fig 11b. Switching Time Waveforms



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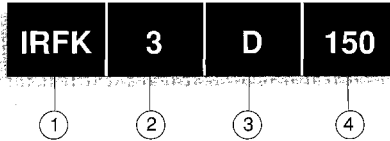
Circuit Configuration and Outline



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Part Numbering



1. - HEX-pak Module.
2. - Number of arms of bridge.
3. - D - Fast switching.
- F - Oscillation resistant for sensitive applications.
4. - Voltage code:-
 - 054 - 60V
 - 150 - 100V
 - 250 - 200V
 - 350 - 400V
 - 450 - 500V
 - C50 - 600V

WORLD HEADQUARTERS: 233 Kansas St., **EL SEGUNDO**, California 90245, USA. Tel:(213) 772-2000. Tlx:694464. Fax:(213) 772-9028
EUROPEAN HEADQUARTERS: Hurst Green, **OXTED**, Surrey RH8 9BB, UK. Tel:(0883) 713215. Tlx:95219. Fax:(0883)714234.

CANADA: 101 Bentley St., Markham, **ONTARIO L3R 3L1**, Tel:(416)475-1897. Tlx:06-966-650. Fax:(416)475-8801
CZECHOSLOVAKIA: Mácurova 19/1565, Box 30, 149 00 **PRAGUE**, Tel:(2) 732 6831. Fax:(2) 732 6831
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FINLAND: **Bliskogsvägen 19**, 02580 **Sjundeå St.**, Tel:(0) 282 8144. Fax:(0) 282 8150.
GERMANY: Saalburgstr. 157, D-6380 **BAD HOMBURG**, Tel:(0)172 37066. Tlx:410404. Fax:(0)172 37055.
HUNGARY: Szent Istvan Park 15, H-1137 **BUDAPEST**, Tel:(1) 1298 822. Fax:(1) 1298 822.
HONG KONG: 202 Peter Building, 60 Queens Road Central, **HONG KONG**, Tel:(85) 252 36355. Fax: (85) 284 52308
ITALY: Via Liguria 49, 10071 Borgaro, **TORINO**, Tel:(0)11470 14 84. Tlx:221257. Fax:(0)11470 42 30.
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INDIA: 31 Greenacre, 5 Union Park, Khar (W), **BOMBAY 400 052**, Tel:(022)535026/533779/540242. Tlx:011-71481.
JAPAN: K & H Bldg. 2F, 3-30-4 Nishi-Ikebukuro, Toshima-ku, **TOKYO**, Japan 171. Tel:(03)983 0641. Fax:(03)983 0642.
SINGAPORE: HEX 10-01 Fortune Centre, 190 Middle Road, **SINGAPORE 0718**, Tel:(85)336 3322/337 4695/336 6286. Fax: (65)337 4692.
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U.S.A.:
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